# Silicon Carbide Schottky Diode

## 650 V, 50 A

#### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

#### Features

- Max Junction Temperature 175°C
- Avalanche Rated 240 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

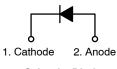
#### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



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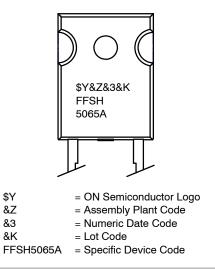


Schottky Diode



TO-247-2LD CASE 340CL

#### MARKING DIAGRAM



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

Symbol	Parameter	Value	Unit		
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		240	mJ	
IF	Continuous Rectified Forward Current @ T <sub>C</sub> < 144°C		50	А	
	Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C		60		
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	1400	А	
		T <sub>C</sub> = 150°C, 10 μs	1300	А	
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	230	А	
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	120	А	
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	429	W	
		T <sub>C</sub> = 150°C	72	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
	TO-247 Mounting Torque, M3 Screw	60	Ncm		

#### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $E_{AS}$  of 240 mJ is based on starting  $T_J = 25^{\circ}$ C, L = 0.5 mH,  $I_{AS} = 31$  A, V = 50 V.

#### **THERMAL CHARACTERISTICS**

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.35	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 50 A, T <sub>C</sub> = 25°C	-	1.51	1.75	V
		I <sub>F</sub> = 50 A, T <sub>C</sub> = 125°C	-	1.67	2.0	
		I <sub>F</sub> = 50 A, T <sub>C</sub> = 175°C	-	1.82	2.4	1
I <sub>R</sub>	Reverse Current	$V_{R} = 650 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	-	200	μΑ
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$	-	-	400	
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 175^{\circ}\text{C}$	-	-	600	
Q <sub>C</sub>	Total Capacitive Charge	V = 400 V	-	147	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	2530	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	271	-	1
		V <sub>R</sub> = 400 V, f = 100 kHz	-	211	_	1

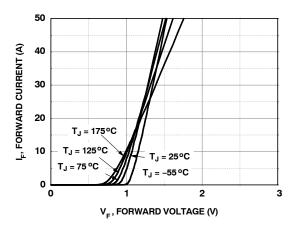
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse: Test Pulse width = 300 μs, Duty Cycle = 2%.

#### **ORDERING INFORMATION**

Part Number	Top Marking	Package	Packing Method	Quantity
FFSH5065A	FFSH5065A	TO-247-2LD (Pb-Free / Halogen Free)	Tube	30 Units

#### **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 



**Figure 1. Forward Characteristics** 

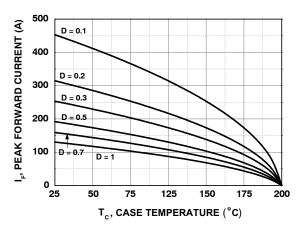


Figure 3. Current Derating

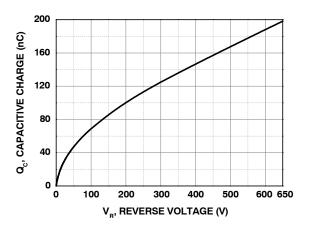


Figure 5. Capacitive Charge vs. Reverse Voltage

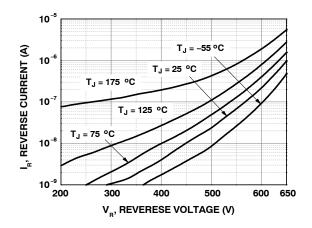


Figure 2. Reverse Characteristics

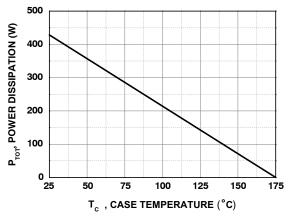


Figure 4. Power Derating

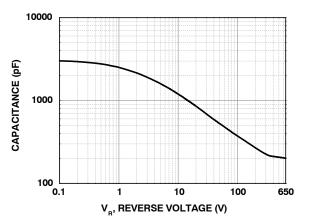


Figure 6. Capacitance vs. Reverse Voltage

#### **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C unless otherwise noted)

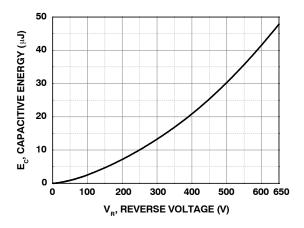


Figure 7. Capacitance Stored Energy

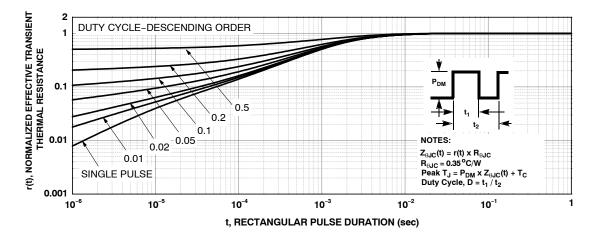


Figure 8. Junction-to-Case Transient Thermal Response Curve

#### **TEST CIRCUIT AND WAVEFORMS**

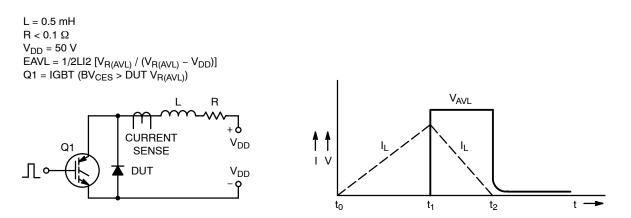


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

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**MILLIMETERS** 

NOM

4.70

2.40

1.50

1.26

1.65

0.61

20.57

16.57

0.93

15.62

~

5.08

11.12

16.00

3.81

3.58

6.73

5.46

5.46

MAX

4.82

2.66

1.70

1.35

1.77

0.71

20.82

16.77

1.35

15.87

~

5.20

~

16.25

3.93

3.65

6.85

5.58

5.58

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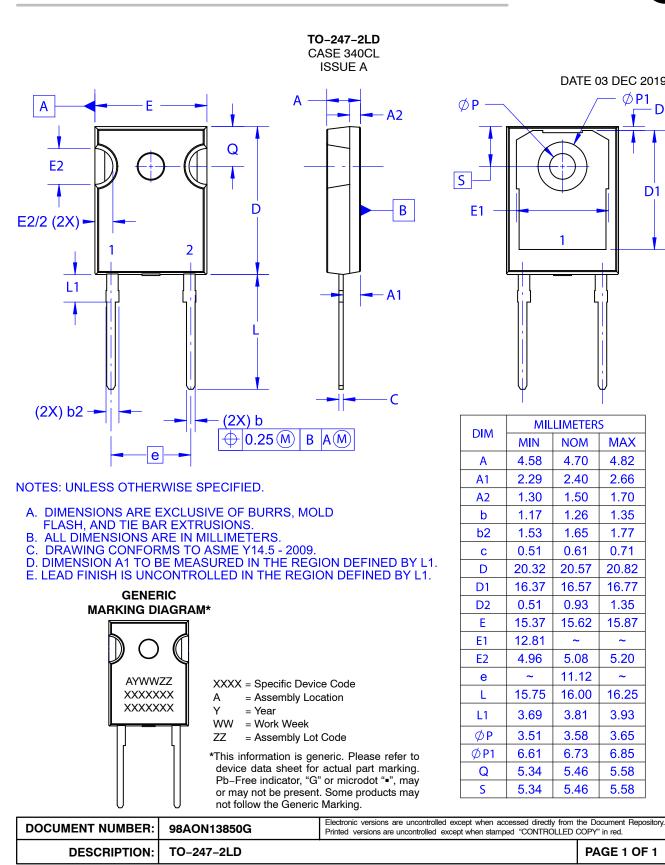
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